Effect of Composition and Annealing on Structural and Optical Properties of $(ZnO)_{1-X}$ $(TiO_2)_X$ Thin Films Prepared by Sol-Gel Method

¹Huda L. Nida, ²Abdulkader J. Muhammad, ³Ali I. Salih

^{1,2,3}Department of Physics / College of Science / University of Kirkuk

¹hudalateef@yahoo.com, ²Abdulkader_jm@yahoo.com, ³aliismailsalih@yahoo.com

Received date: 5 / 3 / 2015 Accepted date: 2 / 6 / 2015

ABSTRACT

Keywords: $(ZnO)_{1-x}(TiO_2)_x$ thin-film, composition, annealing, energy-gap, Urbach-energy.

تأثير التركيب والتلدين على الخصائص التركيبية والبصرية لأغشية ($_{ m X}({ m TiO}_2)_{ m X}$) المحتضرة بطريقة السائل الهلامي

هدى لطيف نده 1 ، علي اسماعيل صالح 2 ، عبدالقادر جليل محمد 3 قسم الفيز ياء / كلية العلو م / جامعة كر كو ك

¹hudalateef@yahoo.com, ²Abdulkader_jm@yahoo.com, ³aliismailsalih@yahoo.com

تاريخ قبول البحث: 2 / 6 / 2015

تاريخ استلام البحث: 5 / 3 / 2015

الملخص

الدراسة تصف تأثير نسبة المزج (x) ودرجة حرارة التلدين (T_a) على الخصائص التركيبية والبصرية رقيقة من الدراسة تصف تأثير نسبة المزج (x) ودرجة حرارة التلدين (T_a) على التجريبية واقتراح معادلات نظرية لفجوة—الطاقة البصرية (T_a) وطاقة أورباخ (T_a) بدلالة تغيرهما مع كل من (T_a) و(T_a). مع زيادة (T_a) وطاقة أورباخ (T_a) بدلالة تغيرهما مع كل من (T_a) ور T_a). مع زيادة (T_a) وطاقة أورباخ (T_a) بدلالة تغيرهما مع كل من (T_a) ور T_a مع زيادة (T_a) وطاقة أورباخ (T_a) بدلالة تغيرهما مع كل من (T_a) ور T_a مع زيادة (T_a) التركيب، وأن (T_a). لقد تم تفسيرتصوف فجوة—الطاقة بالأشارة إلى أن زيادة (T_a) سيزيد من عشوائية تكرارية (أو دورية) االتركيب، وأن درجة حرارة التلدين (T_a) من تجعل التركيب يتراخى بشكل أفضل نحو الصيغ البلورية . زيادة (T_a) أصغر من كتلة أيونات الزنك (T_a). بشكل عام فإن عمل التركيب يهدم الصيغ البلورية التي تلاحظ في ألاغشية النقية لـ (T_a) و لـ (T_a)، ولكن التلدين يعمل على تحسين نوعية الأغشية من حيث درجة التركيب البلوري.

الكلمات الدالة: أغشية رقيقة (XnO)1-x(TiO2)x)، التركيب، التلدين، فجوة الطاقة، طاقة أورباخ.

1.INTRODUCTION

Oxides of zinc (ZnO) and titanium (TiO2) attracted the attention of researchers for years for their potential use in various applications. The applications cover a wide range including Surface-

Acoustic-Wave (SAW) Devices, LEDs, solar-cells, transparent- electrodes and displays [1-6].

Composites and/or bi-layers of ZnO and TiO2 are also considered for these applications by various

groups of researchers [7-9]. Efforts to improve characteristics and/or performance is still required

and ongoing [10-15].

The method of preparation and post annealing are considered as important parameters to improve

film quality and device performance.

In this study we report results of investigations carried out in order to study the effect of

composition and annealing-temperature on structural, and optical properties of composite thin-films

of $(ZnO)_{1-x}(TiO_2)_x$ prepared by sol-gel method for values of x from x=0.05 up to x=0.25 and

annealing-temperatures of (400, 500, and 600) C. The sol-gel process has the advantage of

simplicity and it is cost effective. X-ray diffraction (XRD), atomic-force-microscopy (AFM), and

UV-VIS-NIR spectroscopy were used for characterization.

2.EXPERIMENTAL DETAILS

2.1. Sample preparation:

Thin films of oxides of ZnO, TiO₂ and $(ZnO)_{1-X}$ (TiO₂)_X with x=(5%,10%,15%,20%,25%)

were deposited on glass substrates(76.2×25.4×1 mm) using sol-gel spin coating technique. The

glass substrates were cleaned with acetone and then in ethanol for 20 min. The slides were

removed from the ethanol and dried with special paper at room temperature.

ZnO solution with 0.5 molarities was prepared by dissolving Zinc acetate { Zn (CH₃Coo)₂

:2H₂O} in ethanol solution and stirring it at 60°C for 5 min after that we add Diethanolamine;

DEA ($C_4H_{11}NO_2$) at a rate of one drop /sec, the mixture solution stirred at 60°C for 2.0 h to

obtain clear light solution which statically aged at room temperature for 24 h. Similarly, TiO₂

solution was prepared by dissolving Tetra Butyl Titanate (TBT) in ethanol solution instead of

Zinc acetate. For the composite structure; $(ZnO)_{1-x}/(TiO_2)_x$ we add (0.85, 1.7, 2.55, 3.4, 4.25)

Web Site: www.kujss.com Email: kirkukjoursci@yahoo.com,

Kirkuk University Journal /Scientific Studies (KUJSS)

Volume 10, Issue 3, September 2015 , p.p(303-319) ISSN 1992 – 0849

ml) of TiO_2 solution to 10 ml of ZnO solution in order to prepare (5%, 10%, 15%, 20%, 25%) of ZnO/TiO_2 composites respectively.

After preparing the sol-gels we deposit it on the glass substrate using a spin coater with 3000 rps for 30 sec. After deposition, the films were dried at 300°C for 10 min to evaporate the solvent and remove organic residuals. Then, the films were finally post annealing at three temperatures; 400, 500, and 600°C.

2.2. Characterization:

X-ray diffraction records were obtained using X-Ray diffraction- SHIMADZU (Cu-Kα).in Nanotechnology &Advanced Materials research center, university of technology. The atomic force microscopy (AFM) measurements were done using model (AA3000) scanning prop microscope through the courtesy of college of science, university of Baghdad. The spectrophotometric data were recorded using double-beam Jenway 7315 spectrophotometer. The thickness of the films was measured by the method of fringes using sodium light.[16]

3. RESULTS AND DISCUSSION

3.1.Structural properties:

Figure (1) shows the XRD-spectrum of some ZnO films post annealed at(400, 500, and $600)^{O}$ C. The figure shows that annealing does improve quality of the film interms of its degree of crystal structure. Similar results for TiO₂ films are shown in Figure (2). Figure (3) displays XRD-spectrum for $(ZnO)_{1-x}(TiO_2)_x$ composite films post annealed at 600 oC for values of x from 5% to 25%



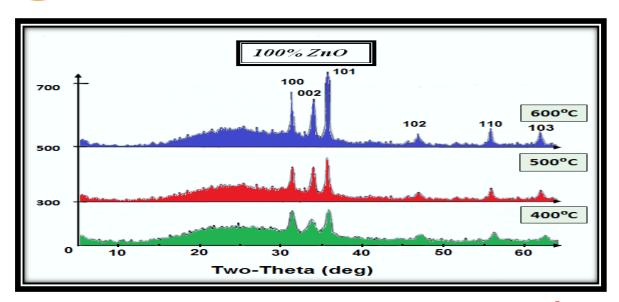


Figure (1): XRD-spectrum for pure ZnO films annealed at (400, 500, and 600) C. The degree of crystallinity improves as the annealing temperature increases.

From figure it is observed that increasing annealing temperature led to an increase in peaks intensity with a decrease in the width of the peaks middle (Full Width at Half Maximum) due to enhances in crystal structure as a result of heat treatment which reduced the crystalline defects, also it's observed that all films have polycrystalline structure with the presence of several peaks belongs to ZnO wurtizite hexagonal structure with dominate (hkl) equal to (101). The results are compatible to JCPD No (36-1451) [17] and in good agreement with [18], and [19]. Figure (2) for pure TiO₂ diffraction peaks are (101,004,200, 221, and 204) for anatase phase and (110,101, and 211) for rutile phase, no Brookite phases are observed in XRD-pattren, results are in good agreement with those given in JCPD data card (JCPDS No. 21 – 1272 & 21 – 1297) [17] for TiO₂ anatase and rutile. It was observed that the intensities of TiO₂ peaks increased slightly with the increase of annealing temperature. This means that TiO₂ films have been crystallized in a tetragonal mixed anatase and rutile form. However, the Full Width at Half Maxima FWHM of the (101) peaks was hardly changed with increasing film annealing temperature, this goes in agreement with the previous works [20], [21], and [22]. The XRD of composite (ZnO/TiO₂) films with pointed characteristic peaks of anatase, rutile, and zinc oxide is presented in Figure (3), The peaks of TiO_2 phases that appear in XRD pattren are for anatase, (101) at $2\theta = 25.281$, (112)

at $2\theta = 38.575$,(200) at $2\theta = 48.049$,and (105) at $2\theta = 53.89$. For rutile phase peaks are (110) at $2\theta = 27.446$,(111) at $2\theta = 41.225$,(210) at $2\theta = 44.05$,and (211) at $2\theta = 54.322$. The appearance of TiO_2 phases can be explained by the high composite percentage of TiO_2 , so Ti-O entered as substitution atom within the crystalline Zn-O oxide pattern. Results are in good agreement with [23] who study pure ZnO & TiO_2 and composite (ZnO) 90% with TiO_2 (10%). In addition, the location of the stronger peaks is shifted to lower 2θ angles because of the increasing in interplanar spacing caused by crystal defects like strain as shown in Table (1)&(2).

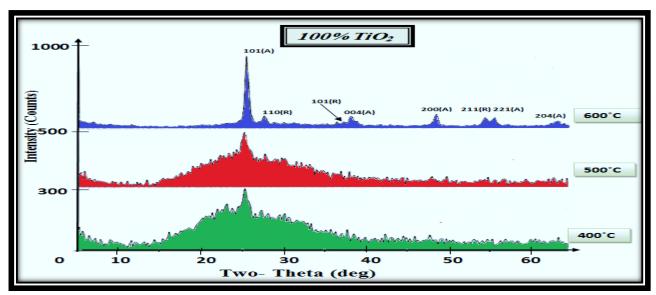


Figure (2): XRD-spectrum for pure TiO₂ films post annealed at 400 ^oC, 500 ^oC, and 600 ^oC. The degree of crystalinity improves as the annealing temperature increases

Table (1): Inter planner spacing with corresponding diffraction angle for pure ZnO&TiO₂ films annealing at (400,500, and 600) ${}^{o}C$.

	T=400 °C		T=50	0 °C	T=600 °C		
Samples	2θ	d(101) Å	2θ	d (d(101) Å	2θ	d(101) Å	
100%ZnO	36.290	2.4737	36.278	2.4745	36.281	2.4743	
100%TiO ₂	25.566	3.4813	25.475	3.4936	25.251	3.5242	

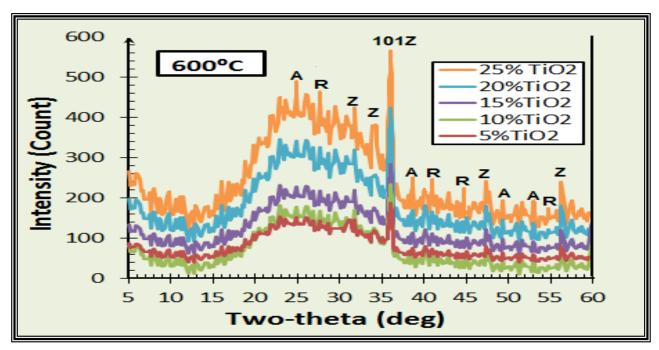


Figure (3): XRD-spectrum for $(ZnO)_{1-X}(TiO_2)_X$ composite films post annealed at 600 $^{\circ}C$ for values of x ranges from 5% to 25% in steps of 5%. The composite films are obviously non-crystalline. (A&R represents Anatase & Rutile phases of TiO2, Z represent ZnO phase).

Table (2): Inter planner spacing with corresponding diffraction angle for $(ZnO)_{1-x}(TiO_2)_x$ films annealing at $600^{\circ}C$.

Sample (ZnO) _{1-x} (TiO ₂) _x	Composition-parameter x						
	0	0.05	0.10	0.20	0.25	1.0	
20	36.281	36.264	36.253	36.243	36.215	25.251	
d (101) Å	2.4743	2.4754	2.4762	2.4768	2.4787	3.5242	

Volume 10, Issue 3, September 2015, p.p(303-319) ISSN 1992 – 0849

The AFM-scans for some samples post annealed at 600° C are shown in Figure (4). The samples include (100%ZnO), (100% TiO₂), (95%ZnO/5% TiO₂) and (75%ZnO/25% TiO₂). These scans support the XRD results. The average-diameter of the grains and the average-roughness of the surface are best for the 5% sample. Table (3) displays some representative data for average-diameter of grains and the average value of surface-roughness, in nanometers, for x= 0, 0.05, 0.10, 0.20, 0.25, and x=1.0 for films post annealed at 600. Our results are in good agreement with [24]

Table (3): Values of average-diameter of grains (crystallites) and the average - roughness parameter as obtained from AFM-scans for a number of samples annealed at 600 °C.

Sample (ZnO) _{1-x} (TiO ₂) _x	Composition-parameter x					
	0	0.05	0.10	0.20	0.25	1.0
Average-diameter [nm]	72.92	83.54	90.69	73.39	78.68	74.74
Average-Roughness [nm]	5.63	0.90	1.75	1.89	1.35	1.42

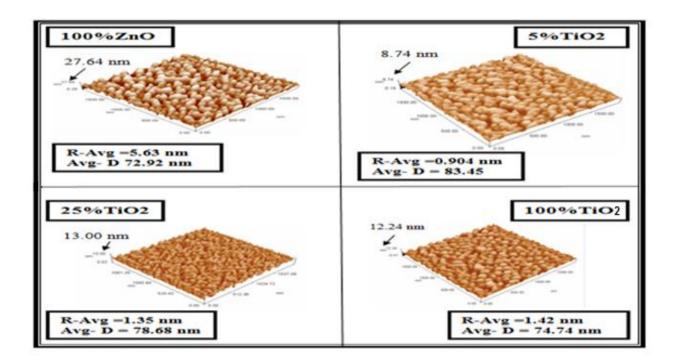


Figure (4): AFM-scans for $(ZnO)_{1-x}(TiO_2)_x$ films post annealed at 600 $^{\circ}$ C for values of x=0.0,0.05,0.25,and 1.(R-Avg=Roughness average and Avg –D=Average diameter).

3.2. Optical properties:

The measured absorbance, transmittance and reflectance of the films which were post annealed at 400 $^{\rm O}$ C, 500 $^{\rm O}$ C, and 600 $^{\rm O}$ C were plotted, it was found that the properties deteriorates; both the absorbance, and reflectance increases while the transmittance decreases as the temperature of annealing is increased, due to heat treatment increase the regularity of the internal arrangement of the atoms and reduce structural defects ,or could be explained by the increased surface roughness of the deposited films as confirmed by AFM[18] The absorption-coefficient (α), refractive-index (α), and extinction coefficient (α) are calculated from the following relations [25]:

$$\alpha = 2.303(\frac{A}{t})$$
(1).

$$n = \frac{1+\sqrt{R}}{1-\sqrt{R}} \qquad \dots (2).$$

$$\kappa = \frac{\alpha \lambda}{4\pi} \qquad \dots (3).$$

Where, λ is the wavelength, A is the absorbance, R is the reflectance and t is the film thickness.

Plots of (α) ,(κ), and (n) (not shown because of lack of space) shows that both α and κ increases with increasing annealing temperature, this behavior attributed to the formation of localized levels near connectivity edge,. The absorption- edge (the cutoff wavelength λ_C) shifts marginally towards longer wavelengths. A peak shows in the plot of the refractive-index n, in the range of 370-380 nm wavelengths A similar peak was observed by [18] for pure ZnO films prepared by sol-gel method. Values of α , κ , n, and λ_C for $(ZnO)_{1-x}(TiO_2)_x$ films,; at λ =330 nm in the absorption-band, as shown in Table (4).

Table (4): Values of α , κ , n, and λ_C for $(ZnO)_{1-X}(TiO_2)_X$ films at a wavelength $\lambda = 330$ nm in the absorption-band.

	Рр	Films					
	parameter	x=0.0	x=0.05	x=0.10	x=0.20	x=0.25	
	α[cm ⁻¹]	68869	80839	78445	72859	70465	
္ပင	n	1. 27	1.4	1.46	1.8	1.9	
400 °C	K	0.1809	0.2124	0.2061	0.1914	0.1851	
	λ _C [nm]	376	378	379	380	380	
	α[cm ⁻¹]	74455	86425	84031	78445	76051	
သ	n	1.57	1.68	1.8	2.2	2.4	
200 °C	K	0.1956	0.2271	0.2207	0.2061	0.1998	
	λ _C [nm]	378	379	380	381	382	
	α[cm ⁻¹]	82276	90416	88022	84031	81637	
သ့	n	1.94	1.8	2.04	2.26	2.6	
ک _ه 009	K	0.2103	0.2379	0.2313	0.2208	0.2145	
	$\lambda_{\mathbf{C}}[\mathbf{nm}]$	379	380	381	383	384	

3.3. Energy gap and Urbach energy:

The Optical energy gap Eg and absorption coefficient α are related by the equation $\alpha = (\frac{\beta}{h\nu})$ (hv-Eg) $^{\gamma}$ (4)

Where k=a constant, h=Planck's constant h=Planck have a direct allowed band gap and h=Planck is a number which characterizes the nature of electronic transition between valance band and conduction band. Our films have $a>10^4$ so they have a direct allowed band gap and for direct allowed transitions h=Planck and h=Planck so they have a direct allowed band gap and for direct allowed transitions h=Planck and h=Planck so they have a direct allowed band gap and for direct allowed transitions h=Planck and h=Planck so they have a direct allowed band gap and for direct allowed transitions h=Planck and h=Planck so they have a direct allowed band gap and for direct allowed transitions h=Planck and h=Planck so they have a direct allowed band gap and for direct allowed transitions h=Planck and h=Planck so they have a direct allowed band gap and for direct allowed transitions h=Planck so they have a direct allowed band gap and for direct allowed transitions h=Planck so they have a direct allowed band gap and for direct allowed transitions h=Planck so they have a direct allowed band gap and for direct allowed transitions h=Planck so they have a direct allowed band gap and for direct allowed transitions h=Planck so they have a direct allowed band gap and for direct allowed transitions h=Planck so they have a direct allowed band gap and for direct allowed transitions h=Planck so they have a direct allowed band gap and for direct allowed transitions h=Planck so they have h=Planck so

$$\alpha = (\frac{\beta}{hv}) \text{ (hv-Eg)}^{1/2} \text{ which gives } (\alpha hv)^2 = \beta (hv - Eg) \dots (5)$$

Where β is a constant independent of photon energy .The optical energy-gap Eg, can be deduced from plots of $(\alpha h v)^2$ -versus-(photon energy h v), where α is the absorption-coefficient, v is the frequency of the electromagnetic-wave[26], while values of what is called Urbach energy Eu, can be deduced from plots of $ln(\alpha)$ -versus-h v, in accordance with the following relation [27] $\alpha = \alpha_0 \exp(h v / E_u)$ (6).

Figure (5) shows plots suggested by equation 5, plots suggested by equation 6 were also done but not shown for lack of space. Values of E_g and E_u obtained from the corresponding plots are shown in Table (5). We note from Table that E_g generally decreases slightly with increasing annealing temperature. The value of E_g obtained is close to the values reported by [28] (3.26-3.29 eV), by [29] (3.24-3.40 eV), by [30] (3.24 eV), by [31] (3.27 eV) and by [32] (3.26-3.34 eV).

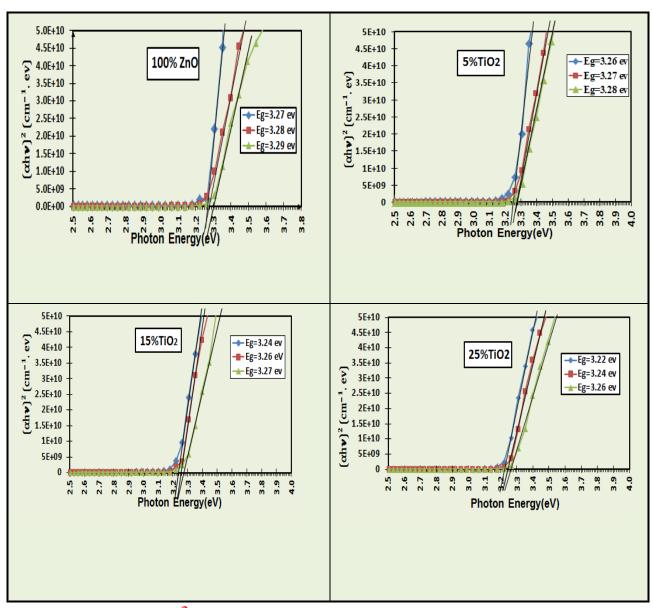


Figure (5): Plots of $(\alpha h v)^2$ -versus-(photon energy h v) for $(\text{ZnO})_{1-x}(\text{TiO}_2)_x$ composite films post annealed at 400 $^{\circ}$ C, 500 $^{\circ}$ C, and 600 $^{\circ}$ C, for x=0.0, 0.05, 0.15 and 0.25.

Reference [33] reports somewhat lower values for ZnO films (2.81-2.98 eV) and composite 1:1 ZnO/TiO₂ films (2.71-2.88 eV) as a function of film-thickness (t); t=897-4884 nm for ZnO and t=890-3920 nm for the composite 1:1 ZnO/TiO₂ films. Also Eg values generally decreases

with increasing TiO₂ content in the $(ZnO)_{1-X}(TiO_2)_X$ composite films, because composition process led to the emergence some of the crystalline defects which appear tails (Urbach Tails) in the area between the valence and conduction bands within forbidden energy gap (Eg) which mean that composition process led to existence topical energy levels(Urbach energy) inside energy gap, that make the necessary energy (hv) to obtain electronic transitions less, and electrons moving from the valence to conduction band become easierEg .Result are in agreement with [34](for ZnO).

Table (5): Values of energy-gap E_g and Urbach-energy E_u , for $(ZnO)_{1-X}(TiO_2)_X$ films annealed at 400 O C, 500 O C, and 600 O C, and for various compositions.

film	Eg [eV]			E _u [meV]			
	400 °C	500 °C	600 °C	400 °C	500 °C	600 °C	
x=0	3.29	3.28	3.27	52	59	73.4	
x=0.05	3.28	3.27	3.26	56	60	75.1	
x=0.10	3.275	3.265	3.25	58	61	80.8	
x=0.15	3.27	3.26	3.24	59	63	82.5	
x=0.20	3.265	3.25	3.235	64	70	83	
x=0.25	3.26	3.24	3.22	77	78	90	

4.CONCLUSIONS

Noting the results of this study as presented in the Tables and figures shown; one may conclude that, the titania and zinc oxides in the composite film exist as separate phases in form of anatase, rutile(TiO_2 phases) and wurtzite modification(ZnO phase), the dominating phase can be classified as hexagonal wurtzite ZnO, (101) peak at 36.5°, and annealing improve the quality of the film in terms of its degree of crystal structure. Also, E_g decreases with both composition-parameter x and annealing-temperature T_a which can be explained by evoking that increasing x will randomize the crystal periodicity, and that the higher annealing temperature relaxes the structure more towards a better crystalline structure. The increase of Urbach-energy, E_U with increased percentage of TiO_2 in the ZnO matrix was attributed to the lower mass of Ti ions as compared to that of Zn ions.

REFERENCES

- [1] A.Tsukazaki, M. Kubota, A.Ohtomo, T.Onuma, K.Ohantani, H.Ohno, S. F. Chichibu, and M. Kawasaki, "*Blue light-emitting diode based on ZnO*", Japanese Journal of Applied Physics, vol. 44, L643-645, (2005).
- [2] R.Konenkamp, R.C.Word, Godinez, "Ultraviolet Electroluminescence from ZnO/ Polymer hetrojunction Light –Emitting Diodes", Nano Letters, vol. 5, issue 10, 2005-2008, (2005).
- [3] Z. L.Wang, J.Song, "Piezoelectric nanogenerators based on zinc oxide nanowire arrays", Science, vol. 312, pp242-246, (2006).
- [4] M. Gianmouli, and F.Spiliopoulouo, "Effect of morphology of nanostructured ZnO films on the efficiency of dye-sensitized solar colls", Renewable Energy, vol. 41, pp 115-122, (2012).
- [5] B.O'Regan, M.Gratzel, "A low-cost, high-efficiency solar cell based on dye -sensitized colloidal TiO₂ films", Nature, vol. 353, pp 737-740, (1991).
- [6] Y.Chen, E.Stathatos, D.D.Dionysiow, "Sol-gel modified TiO₂ powder films for high performance dye-sensitized solar cells", J. Photochem Photobiol A chem, vol. 203, pp 192-198, (2009).
- [7] S. A.Siuleiman, D. V. Raichev, A. S.Bojinova, D. T.Dimitrov, and K. I.Papazova," *Nanosized composite ZnO/TiO₂ thin films for photocatalytic applications*", Bulgarian Chemical Communications, Volume 45, Number 4, pp 649-654, (2013).
- [8] Horng-Huey Ko, Hui-Ting Chen, Feng-Ling Yen, Wan-Chen Lu, Chih-Wei Kuo and L.Moo-Chin Wang, "Preparation of TiO₂ nanocrystallite powders coated with 9 mol% ZnO for cosmetic applications in sunscreens", International Journal of Molecular Sciences, vol.13, pp 1658-1669, (2012).
- [9] Jayasankar Mani, Hazem Sakeek, Z. Salah Habouti, Matthias Dietze and Mohammed Es-Souni, "Macro-meso-porous TiO₂, ZnO and ZnO-TiO₂-composite thick films. Properties and application to photocatalysis", Catalysis Science & Technology, vol. 2, pp 379-385, (2012).
- [10] K. E. Kim, et al., "Enhancement in the performance of dye-sensitized solar cells containing ZnO-covered TiO₂ electrodes prepared by thermal chemical vapor deposition", Solar Energy Materials and Solar cells, vol. 91, pp366-370, (2007).

- [11] Rosniza us sin, Kwang-Leong choy and Xianghui Hou, "Fabrication of multilayer ZnO/TiO₂/ZnO thin films with enhancement of optical properties by Atomic Layer Deposition (ALD)", Applied Mechanics and Materials Vols. 465-466, pp 916-921, (2014).
- [12] E.Fortunato, A.Goncalves, A.Marques, Viana A., Aguas H., Pereiera L., Ferreira I., Vilarinho P., and Martins R., "*New developments in gallium doped zinc oxide deposited on polymeric substrates by RF magnetron sputtering*", Surface and Coating Technology, vol. 180, pp 20-25, (2004).
- [13] Yu-Zhu Gu, Hong-Liang Lu, Yang Geng, Zhi-Yuan Ye, Yuan Zhang, Qing-Qing Sun, Shi-Jin Ding and David Wei Zhang," *Optical and microstructural properties of ZnO/TiO2 nanolaminates prepared by atomic layer deposition*". Nanoscale Research Letters, vol. pp 1-5, (2013).
- [14] S.M. Pawar, P. Chougule, D.Godse, D. Jundale, S. Pawar, B. Raut, V. Patil, "Effect of annealing on structure, morphology, electrical and optical properties of nanocrystalline TiO₂ thin films" J. Nano- Electron. Phys, vol. 73.63.Bd, 2011, pp.185-192.
- [15] Lei Zhao, Maosheng Xia, Yuhua Liu, Biju Zheng, Qing Jiang and Jianshe Lian." *Structure and photocatalysis of TiO2/ZnO double-layer film prepared by Pulsed Laser Deposition*", Materials Transactions, Vol. 53, No. 3, pp 463-468, (2012).
- [16] R.M.WHITTLE & J.YARWOOD" *Experimental physics for students*" Chapman and Hall, London,(1973).
- [17] "JCPDS, Joint Committee for Powder Diffraction Standards, Power Diffraction File for Inorganic Materials", No. (21-1272), (21-1276), and (36-1451) (1997).
- [18] Nanda Shakti, "Structural and Optical Properties of Sol-gel Prepared ZnO Thin Film" Applied Physics Research, Vol. 2, No. 1, (2010) PP19-28.
- [19] Jayasankar Mani, Hazem Sakeek, Z Salah Habouti, Matthias Dietze and Mohammed Es-Souni, "Macro-meso-porous TiO2, ZnO and ZnO-TiO2-composite thick films, Properties and application to photocatalysisw" Catalysis Science & Technology, Vol. 2, (2012), PP. 379–385.
- [20] Chennupati Jagadish and Stephen J. Pearton"Zinc Oxide Bulk, Thin Films and Nanostructures" first edition, Hardcover November 22, (2006).

- [21] Ching-Hua Wei and Ching-Min Chang. "Polycrystalline TiO2 Thin Films with Different Thicknesses Deposited on Unheated Substrates Using RF Magnetron Sputtering", Materials Transactions, Vol. 52, No. 3, (2011), PP. 554 559.
- [22] Sarmad S.Kaduory, Dr.Ali A. Yousif Dr.Adawiya J. Haider, and Dr.Khaled Z.Yahya "Synthesis Of Nanostructured TiO2 Thin Films By Pulsed Laser Deposition (PLD) And The Effect Of Annealing Temperature On Structural And Morphological Properties", Eng. & Tech. Journal, Vol 31, Part (B), No. 4, (2013), PP.460-470.
- [23] S. A. Siuleiman, D. V. Raichev, A. S. Bojinova, D. T. Dimitrov, K. I. Papazova, "Nanosized composite ZnO/TiO2 thin films for photocatalyti applications", Bulgarian Chemical Communications, Volume 45, Number 4, (2013), PP. 649–654.
- [24] Rosniza Hussin, Kwang-Leong choy and Xianghui Hou," Fabrication of Multilayer ZnO/TiO2/ZnO Thin Films with Enhancement of Optical Properties by Atomic Layer Deposition (ALD)" Applied Mechanics and Materials Vol. 465, No.466 (2014) PP. 916-921
- [25] J. I.Pankova, "Optical processes in semiconductors", Dover Publications Inc., (1971).
- [26] E.R.Shaaban, E.R." Calculation of the optical constants of amorphous semiconducting As40S60, As40S25Se25and As40Se60 Thin films from transmittance and reflectance measurements". Journal of Applied Sciences, Vol.6, No.2, (2006), PP.340-346.
- [27] A. Boukhachem, B. Ouni, A. Bouzidi, A.Amlouk, K. Boubaker, M. Bouhafs, and M.Amlouk, "Quantum Effects of Indium /Ytterbium Doping on ZnO-Like Nano-Condensed Matter in terms of Urbach-Martienssen and Wemple-DiDomenico Single- Oscillator Models Parameters" Condensed Matter Physics. Vol.1 (2012),PP.1-10.
- [28] J.Sengupta ,R.K. Sahoo, K.K.Bardhan , and C.D.Mukherjee ,"Influence of annealing temperature on the structural, topographical and optical properties of sol-gel derived ZnO thin films", Materials Letters, vol. 65, pp 2572-2574, (2011).
- [29] J.Sengupta, A. Ah R.med, and R.Labar, "Structural and optical properties of post annealed Mg doped ZnO thin films deposited by sol-gel method", Materials Letters, vol. 109, pp 265-268, (2013).



- [30] Z.R.Khan, Khan M. Shoeb, M. Zulfequar, and M. Shahid. Khan, "Optical and structural properties of ZnO thin films fabricated by sol-gel method", Materials Science and Applications, vol. 2, pp 340-345, (2011).
- [31] M.Saravanakumar, S.Agilan, and N.Muthukumarasamy," *Effect of annealing temperature on characterization of ZnO thin films by sol-gel method*", International Journal of Chem Tech Research, vol. 6, pp 2941-2945, (2014).
- [32] K.Huang , Z.Tang ,L. Zhang ,J. Yu , J.Lv,X. Liu , andF. Liu , "Preparation and characterization of Mg-doped ZnO thin films by sol-gel method", Applied Surface Science, vol.258, pp 3710-3713, (2012).
- [33] C.M.Firdausa, M.S.B Shah Rizamb , M. Rusopa , and S.R. Hidayah, "Characterization of ZnO and ZnO:TiO2 thin films prepared by sol-gel spray-spin coating technique", Engineering Procedia, vol. 41, pp 1367-1373, (2012).
- [34] Mohammad M. Ali and Seif M. Meshari." *Structural and Optical Characterization of ZnO Thin Films by Sol-gel Technique*" Journal of Basrah Researches ((Sciences)) Vol. 40. No. 1, (2014),PP.39-48.

AUTHOR



Huda Lattif Nida:- B.Sc./ Physics department, Science College, University of Mosul, (2001-2002), I work in General Directorate of Kirkuk Education, At present I am M.Sc. Student at Physics department, Science College, University of Kirkuk.